

## 1. General description

WeEnPACK-B1 module with WeEn 1200V Gen2 SiC MOSFET and PressFit pin type. Intergrated with NTC temperature sensor.



## 2. Features and benefits

- Dual-boost topology
- Press-fit pin configuration
- Low ON resistance
- Low switching losses
- Reduced  $Q_g$  and  $C_{rss}$
- Minimized circuit impedance
- Robust product design

## 3. Applications

- Solar power MPPT

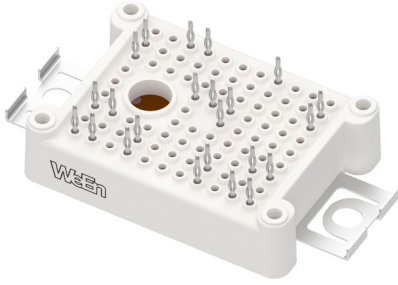
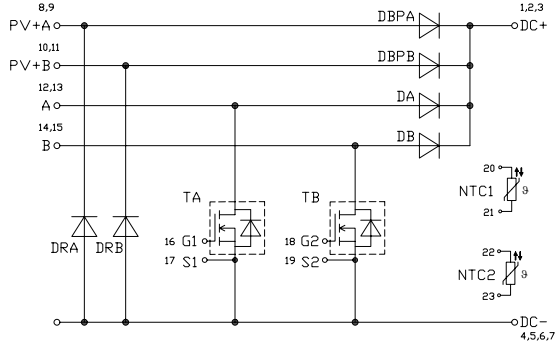
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$		1200			V
$I_D$	drain current	$V_{GS} = 18\text{ V}; T_n = 25\text{ °C}$		45			A
$P_{tot}$	total power dissipation	$T_n = 25\text{ °C}$		86			W
$T_j$	junction temperature			-40 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15\text{ V}; I_D = 40\text{ A}; T_j = 25\text{ °C}$		-	30	-	mΩ
		$V_{GS} = 18\text{ V}; I_D = 40\text{ A}; T_j = 25\text{ °C}$		-	24	40	mΩ
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 40\text{ A}; V_{DS} = 800\text{ V}; V_{GS} = -4\text{ V}/18\text{ V}; T_j = 25\text{ °C}$		-	151	-	nC
$Q_{GD}$	gate-drain charge			-	21	-	nC
<b>Source-drain diode</b>							
$Q_r$	recovered charge	$I_{SD} = 40\text{ A}; di/dt = 500\text{ A}/\mu\text{s}; V_{DS} = 400\text{ V}; T_j = 25\text{ °C}$		-	129	-	nC

### 5. Pinning information

Table 2. Pinning information

Simplified outline	Circuit diagram
 <p>* Please refer to the package outline description for actual pin order.</p>	

### 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WMSC030B12B1P-C	WeEnPACK-B1	WMSC030B12B1P-C6T	Tray	24	WeEnPACK-B1PBT-B	28-Jun-2024

### 7. Marking

Table 4. Marking codes

Type number	Marking codes
WMSC030B12B1P-C	WMSC030B12B1P-C

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$T_{stg}$	storage temperature			-40 to 125	°C
$T_{j,op}$	operating junction temperature			-40 to 150	°C
$T_{j,max}$	maximum junction temperature	Intermittent condition with shortened lifetime		-40 to 175	°C
$V_{ISOL}$	RMS isolation voltage	$T_j = 25\text{ °C}$ ; all terminals shorted; $f = 50\text{ Hz}$ ; $t = 1\text{ s}$		3500	V
<b>MOSFET</b>					
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$		1200	V
$V_{GS,max}$	gate-source voltage	Absolute maximum values		-12 to 24	V
$V_{GS,op}$	gate-source voltage	Recommended operational values		-4 to 18	V
$P_{tot}$	total power dissipation	$T_h = 25\text{ °C}$		86	W
$I_D$	drain current	$V_{GS} = 18\text{ V}$ ; $T_h = 25\text{ °C}$		45	A
		$V_{GS} = 18\text{ V}$ ; $T_h = 100\text{ °C}$		28	A
$I_{DM}$	peak drain current	pulse width $t_p$ limited by $T_{j,max}$		90	A
$E_{as}$	single pulse drain-to-source avalanche	$I_{AS} = 20\text{ A}$ ; $L = 1\text{ mH}$ ; $V_{DD} = 100\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; per MOSFET		200	mJ
<b>Body Diode</b>					
$I_{SD}$	DC body diode forward current	$V_{GS} = -4\text{ V}$ ; $T_h = 25\text{ °C}$		20	A
$I_{SD,pulse}$	Pulse body diode current	verified by design, $t_p$ limited by $T_{j,max}$		90	A
<b>Inverse-polarity Protection Diode</b>					
$V_{RRM}$	repetitive peak reverse voltage			1600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_h \leq 97\text{ °C}$		45	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(init)} = 25\text{ °C}$ ; sine-wave pulse		530	A
		$t_p = 8.3\text{ ms}$ ; $T_{j(init)} = 25\text{ °C}$ ; sine-wave pulse		582	A
<b>Boost Diode</b>					
$V_{RRM}$	repetitive peak reverse voltage			1200	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; square-wave pulse; $T_h \leq 125\text{ °C}$		40	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; square-wave pulse		80	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(init)} = 25\text{ °C}$ ; sine-wave pulse		350	A
		$t_p = 10\text{ }\mu\text{s}$ ; $T_{j(init)} = 25\text{ °C}$ ; sine-wave pulse		2100	A

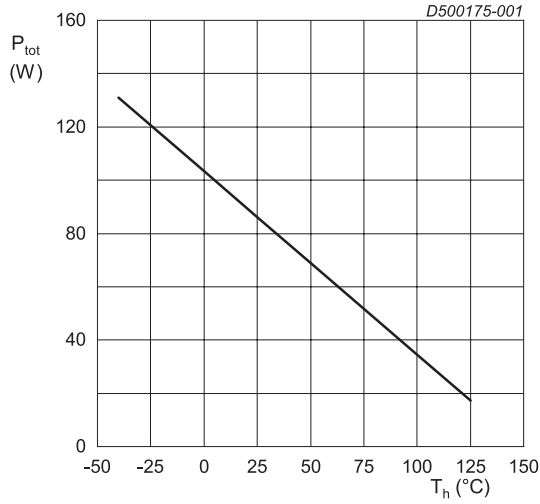


Fig. 1. Power dissipation as a function of heatsink temperature; maximum values

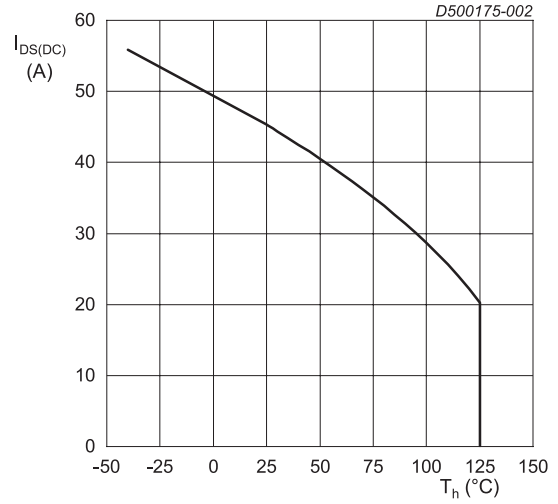


Fig. 2. Continuous Drain Current as a function of heatsink temperature

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	per MOSFET		-	0.6	-	K/W
$R_{th(j-h)}$	thermal resistance from junction to heatsink	per MOSFET, $\lambda_{grease} = 1 \text{ W/(m}\cdot\text{K)}$ $thick_{grease} = 50 \text{ }\mu\text{m}$		-	1.45	-	K/W
<b>Internal Isolation</b>		basic insulation (class 1, IEC 61140)		Al <sub>2</sub> O <sub>3</sub>			
$d_{Creep}$	Creepage distance	terminal to heatsink		-	11.5	-	mm
		terminal to terminal		-	6.3	-	mm
$d_{Clear}$	Clearance	terminal to heatsink		-	10	-	mm
		terminal to terminal		-	5	-	mm
CTI	Comperative tracking index			>200			
F	Mounting force per clamp			20	-	50	N
G	Approximate Weight			-	20	-	g

Note: Module is ESD sensitive. Handling precautions are recommended.

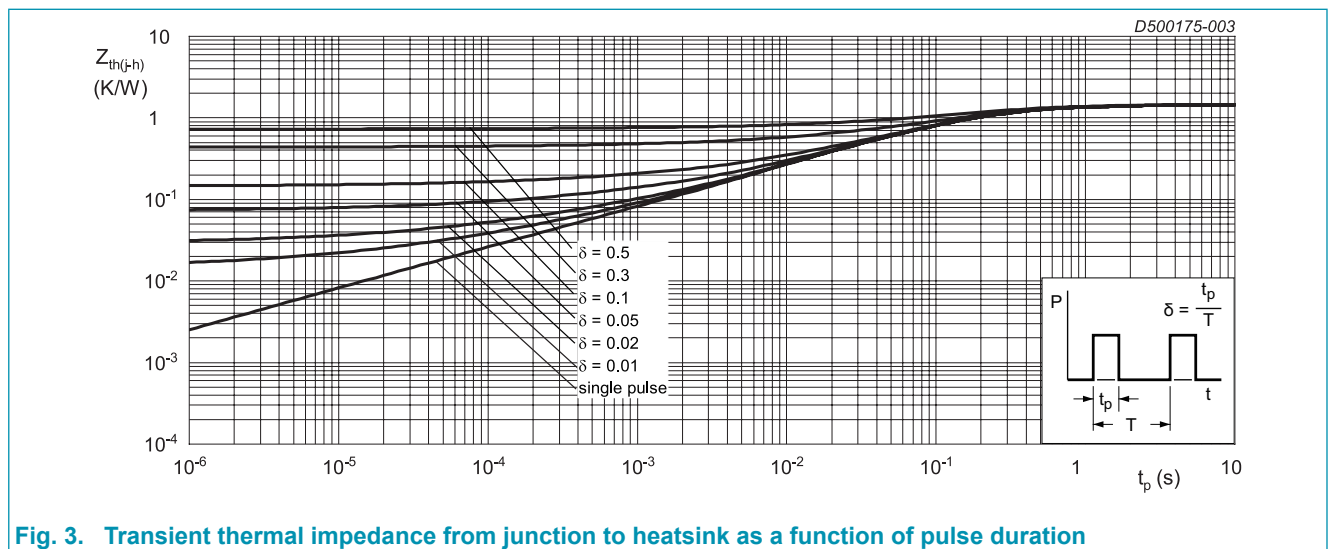


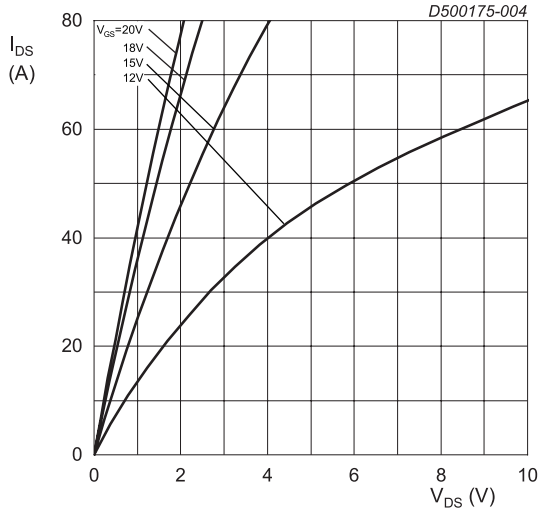
Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse duration

## 10. Characteristics

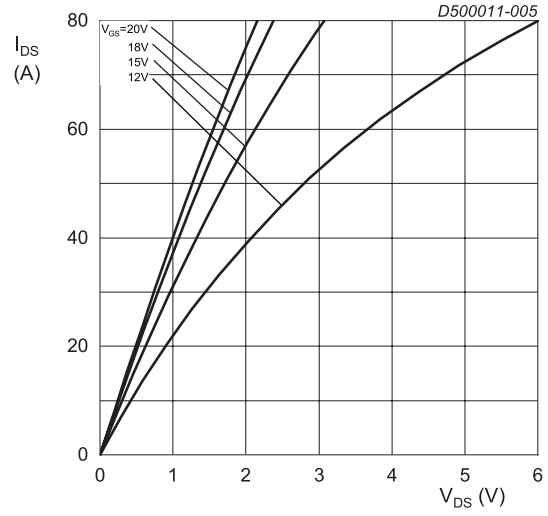
Table 7. Characteristics

MOSFET							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 100 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ\text{C}$		1200	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 12 \text{ mA}; V_{DS} = 10 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$		1.9	2.5	3.5	V
		$I_D = 12 \text{ mA}; V_{DS} = 10 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$		-	1.9	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$		-	0.2	100	$\mu A$
$I_{GSS}$	gate leakage current (absolute value)	$V_{GS} = 24 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$		-	10	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$		-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15 \text{ V}; I_D = 40 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$		-	30	-	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 40 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$		-	24	40	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 40 \text{ A}; T_j = 125 \text{ }^\circ\text{C}$		-	37	-	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 40 \text{ A}; T_j = 150 \text{ }^\circ\text{C}$		-	42	-	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 40 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$		-	48	-	m $\Omega$
$R_G$	gate resistance, each side	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$ , per MOSFET		-	0.8	-	$\Omega$
$g_{fs}$	transconductance	$V_{DS} = 20 \text{ V}; I_D = 40 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$		-	27	-	S
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 40 \text{ A}; V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$		-	151	-	nC
$Q_{GS}$	gate-source charge			-	63	-	nC
$Q_{GD}$	gate-drain charge			-	21	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 1000 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$		-	3305	-	pF
$C_{oss}$	output capacitance			-	139	-	pF
$C_{rss}$	reverse transfer capacitance			-	12	-	pF
$E_{oss}$	Coss stored energy			-	70	-	$\mu J$
$t_{d(on)}$	turn-on delay time		$V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; R_{G(ext)} = 5.1 \text{ } \Omega; I_D = 40 \text{ A}; L = 100 \text{ } \mu H; T_j = 25 \text{ }^\circ\text{C}$		-	32	-
$t_r$	rise time			-	30	-	ns
$t_{d(off)}$	turn-off delay time			-	52	-	ns
$t_f$	fall time			-	11	-	ns
$E_{on}$	turn-on energy			-	597	-	$\mu J$
$E_{off}$	turn-off energy			-	110	-	$\mu J$

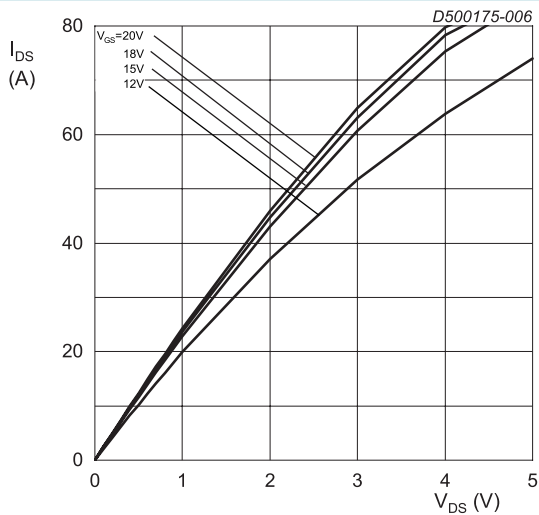
Body diode							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
V <sub>SD</sub>	source-drain voltage	V <sub>GS</sub> = -4 V; I <sub>SD</sub> = 40 A; T <sub>j</sub> = 25 °C		-	5.5	-	V
		V <sub>GS</sub> = -4 V; I <sub>SD</sub> = 40 A; T <sub>j</sub> = 150 °C		-	5.0	-	V
<b>Dynamic characteristics</b>							
I <sub>rrm</sub>	reverse recovery current	I <sub>SD</sub> = 40 A; di/dt = 500 A/μs; V <sub>DS</sub> = 400 V; T <sub>j</sub> = 25 °C		-	6.9	-	A
t <sub>rr</sub>	reverse recovery time			-	33.4	-	ns
Q <sub>r</sub>	recovered charge			-	129	-	nC
<b>Inverse-polarity Protection Diode</b>							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 45 A; T <sub>j</sub> = 25 °C		-	1.20	1.40	V
		I <sub>F</sub> = 45 A; T <sub>j</sub> = 150 °C		-	1.10	1.30	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1600 V; T <sub>j</sub> = 25 °C		-	-	50	μA
		V <sub>R</sub> = 1600 V; T <sub>j</sub> = 150 °C		-	-	1.5	mA
V <sub>R</sub>	reverse voltage	DC		-	1600	-	V
<b>Boost Diode</b>							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 40 A; T <sub>j</sub> = 25 °C		-	1.42	1.60	V
		I <sub>F</sub> = 40 A; T <sub>j</sub> = 150 °C		-	1.90	2.30	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C		-	1	200	μA
V <sub>R</sub>	reverse voltage	DC		-	1200	-	V
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 40 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 500 A/μs; T <sub>j</sub> = 25 °C		-	99	-	nC
<b>NTC thermistor</b>							
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
R <sub>25</sub>	Rated resistance	T <sub>NTC</sub> = 25 °C		-	5000	-	Ω
R <sub>100</sub>		T <sub>NTC</sub> = 100 °C			493±5%		Ω
B <sub>25/50</sub>	B-value	R <sub>2</sub> = R <sub>25</sub> exp[B <sub>25/50</sub> (1/T <sub>2</sub> - 1/(298.15K))]			3380		K
	Maximum operating temperature			-	200	-	°C
	Dissipation costant			-	2	-	mW/K
	Thermal time constant			-	≤10	-	s



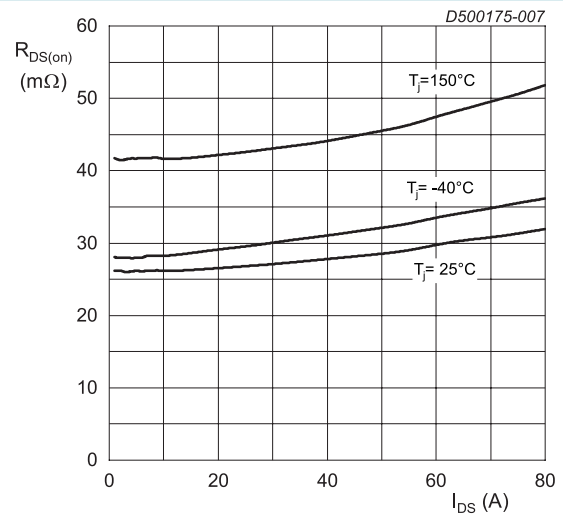
$T_j = -40\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$   
**Fig. 4. Output characteristics; drain current as a function of drain-source voltage; typical values**



$T_j = 25\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$   
**Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values**

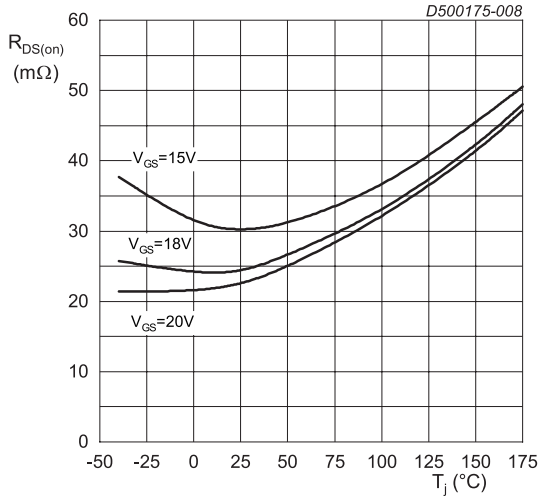


$T_j = 150\text{ }^\circ\text{C}; t_p < 200\text{ }\mu\text{s}$   
**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**

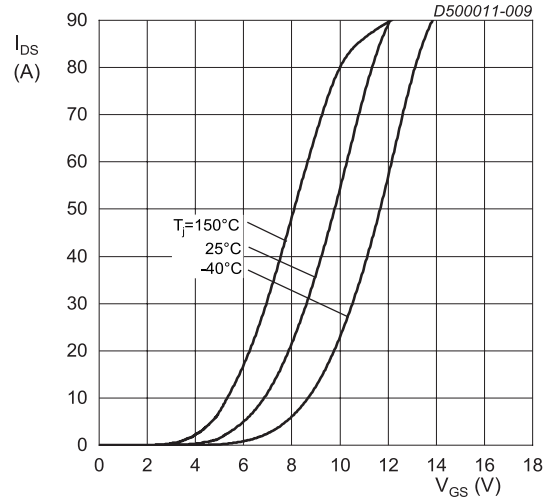


$V_{GS} = 18\text{ V}; t_p < 200\text{ }\mu\text{s}$   
**Fig. 7. Drain-source on-state resistance as a function of drain current; typical values**

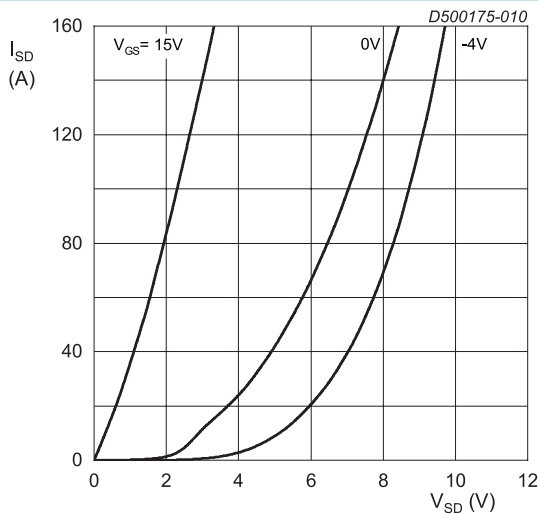




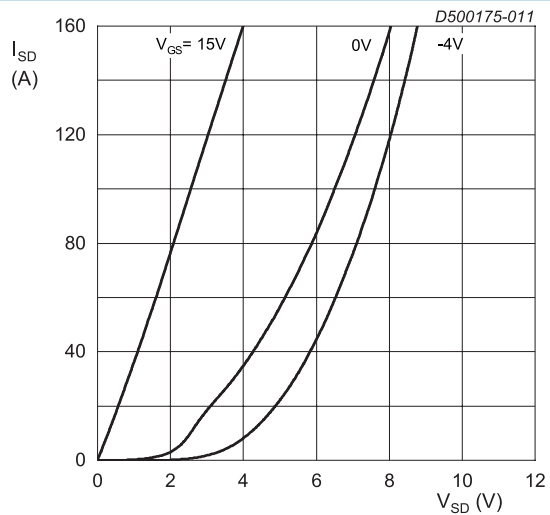
$I_{DS} = 40 A; t_p < 200 \mu s$   
**Fig. 8. Drain-source on-state resistance as a function of junction temperature**



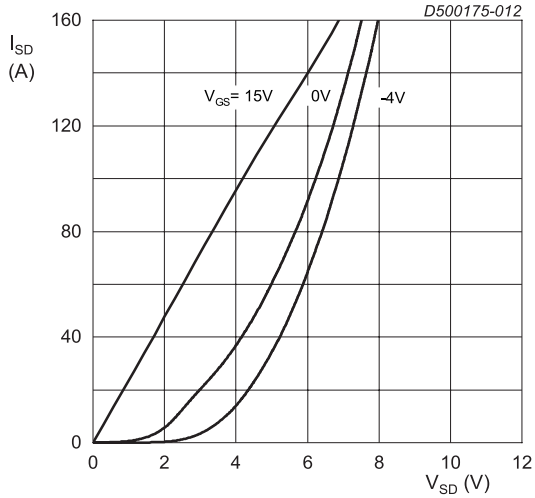
$V_{DS} = 20 V; t_p < 200 \mu s$   
**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



$T_j = -40^{\circ}C; t_p < 200 \mu s$   
**Fig. 10. Body diode forward characteristics; typical values**

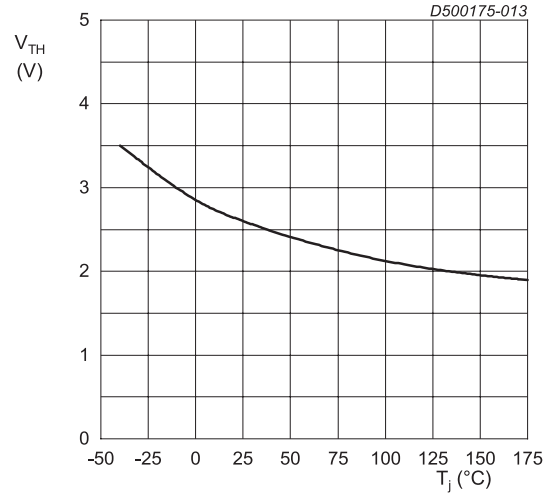


$T_j = 25^{\circ}C; t_p < 200 \mu s$   
**Fig. 11. Body diode forward characteristics; typical values**



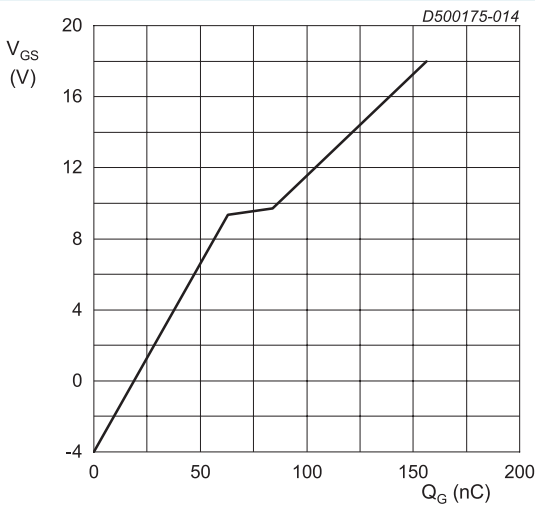
$T_j = 150\text{ }^\circ\text{C}$ ;  $t_p < 200\text{ }\mu\text{s}$

Fig. 12. Body diode forward characteristics; typical values



$V_{DS} = 10\text{ V}$ ;  $I_{DS} = 12\text{ mA}$

Fig. 13. Threshold voltage as a function of junction temperature



$I_{DS} = 40\text{ A}$ ;  $I_{GS} = 0.1\text{ mA}$ ;  $V_{DS} = 800\text{ V}$ ;  $T_j = 25\text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

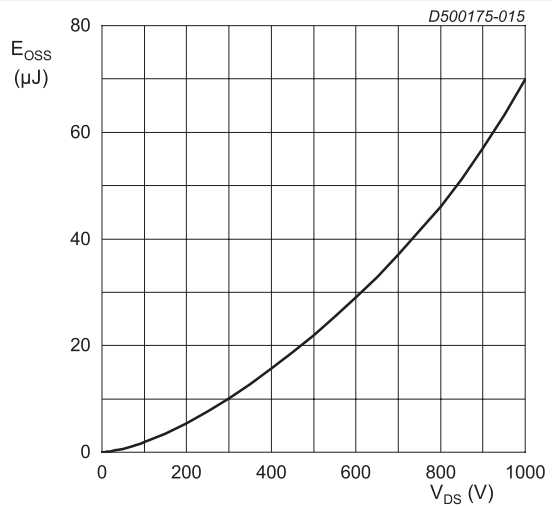
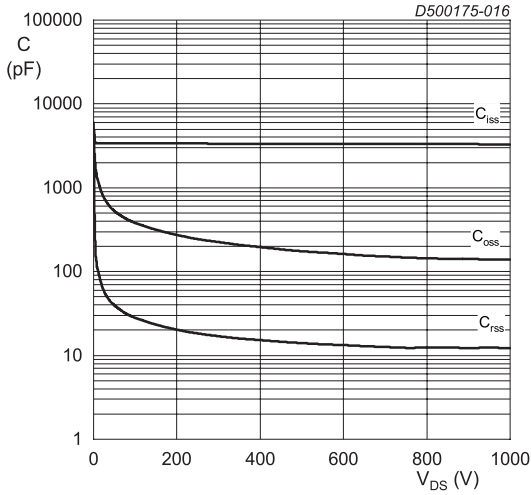
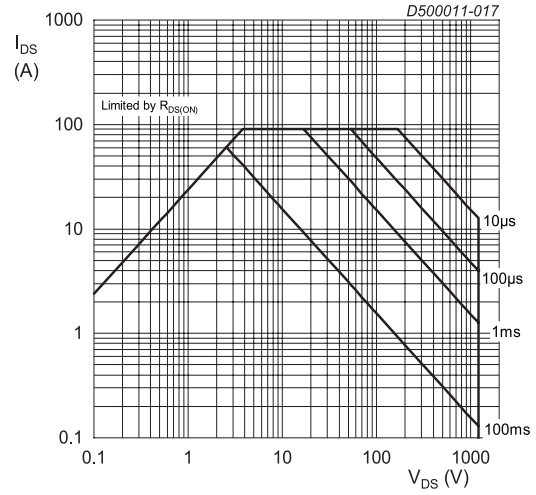


Fig. 15. Output capacitor stored energy as a function of drain-source voltage



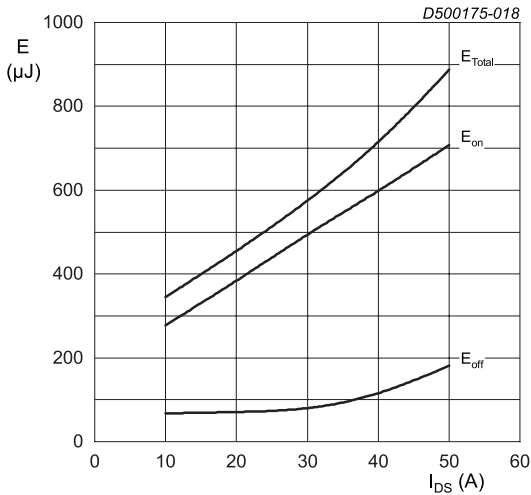
$V_{DS} = 0 - 1000 \text{ V}$   
 $T_j = 25 \text{ }^\circ\text{C}; V_{AC} = 25 \text{ mV}; f = 1 \text{ MHz}$

**Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



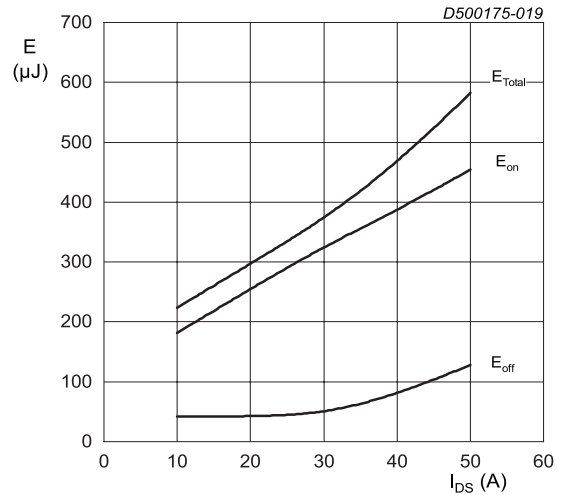
$T_j = 25 \text{ }^\circ\text{C}; D = 0$   
 Parameter:  $t_p$

**Fig. 17. Forward bias safe operating area**



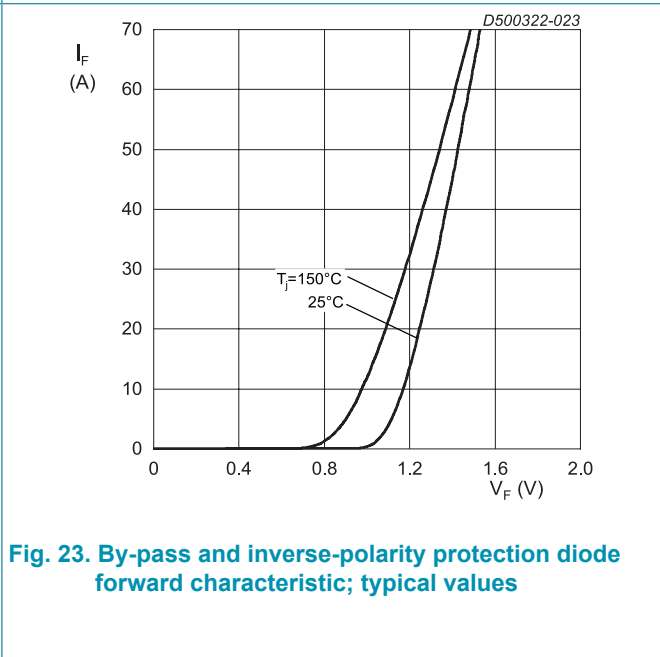
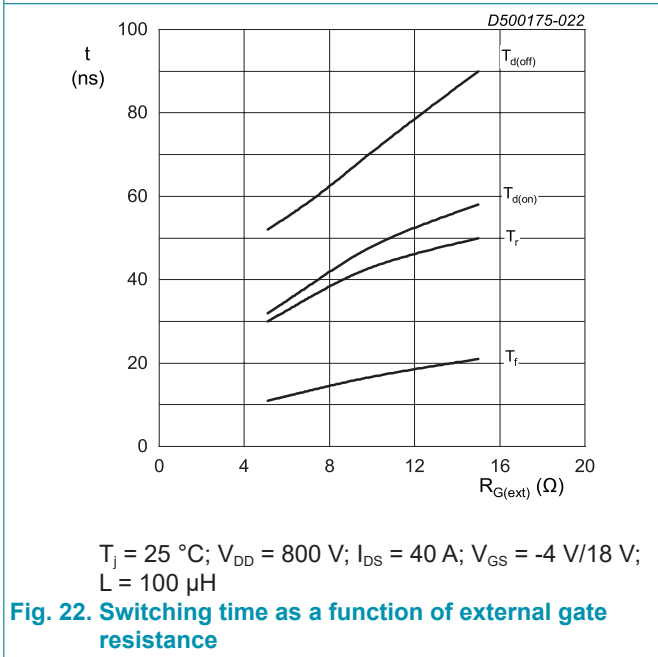
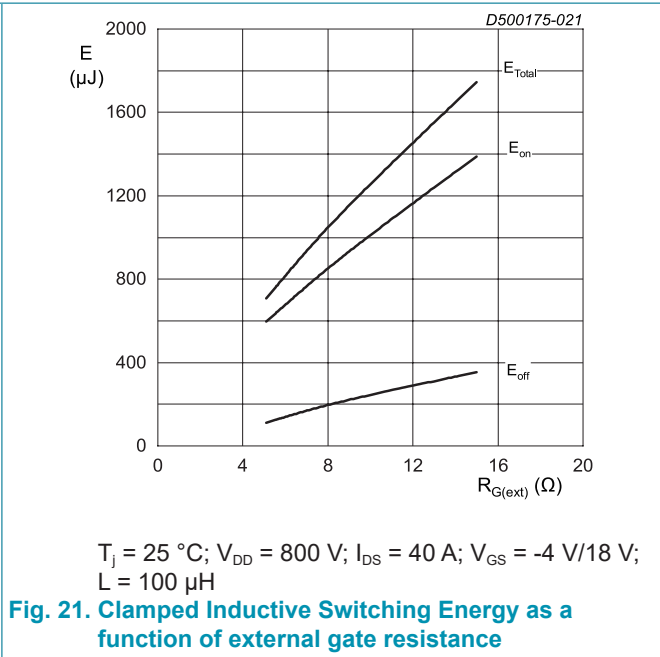
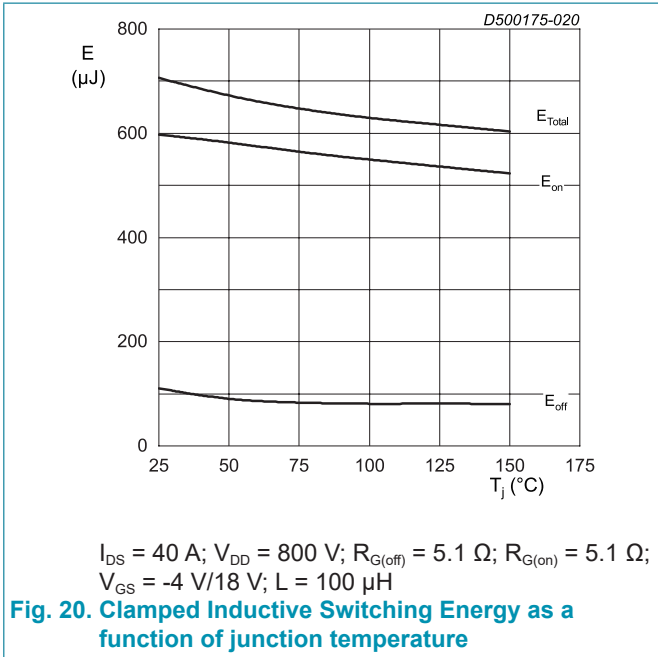
$T_j = 25 \text{ }^\circ\text{C}; V_{DD} = 800 \text{ V}; R_{G(ext)} = 5.1 \text{ } \Omega; R_{G(on)} = 5.1 \text{ } \Omega;$   
 $V_{GS} = -4 \text{ V}/18 \text{ V V}; L = 100 \text{ } \mu\text{H}$

**Fig. 18. Clamped Inductive Switching Energy as a function of drain current**



$T_j = 25 \text{ }^\circ\text{C}; V_{DD} = 600 \text{ V}; R_{G(off)} = 5.1 \text{ } \Omega; R_{G(on)} = 5.1 \text{ } \Omega;$   
 $V_{GS} = -4 \text{ V}/18 \text{ V V}; L = 100 \text{ } \mu\text{H}$

**Fig. 19. Clamped Inductive Switching Energy as a function of drain current**



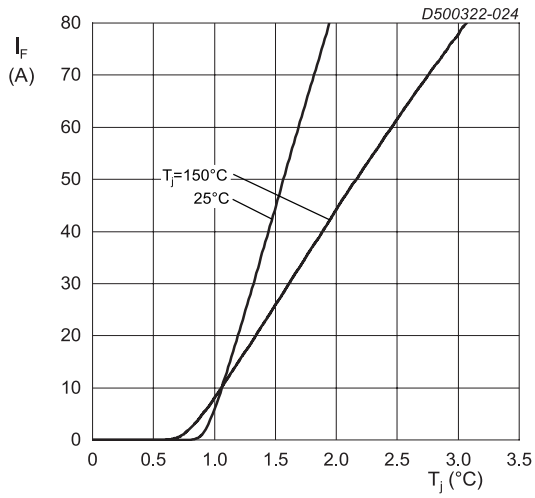


Fig. 24. Boost diode forward characteristic; typical values

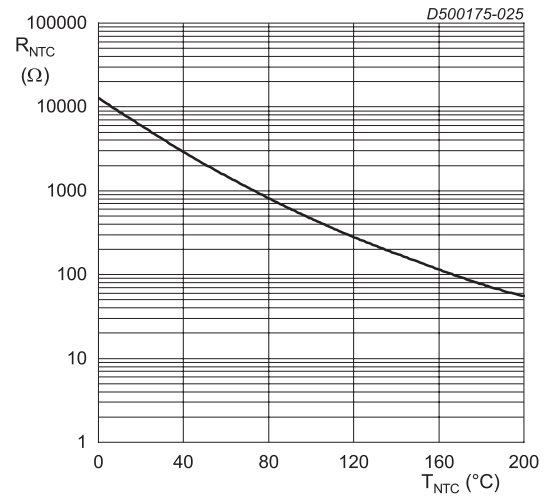
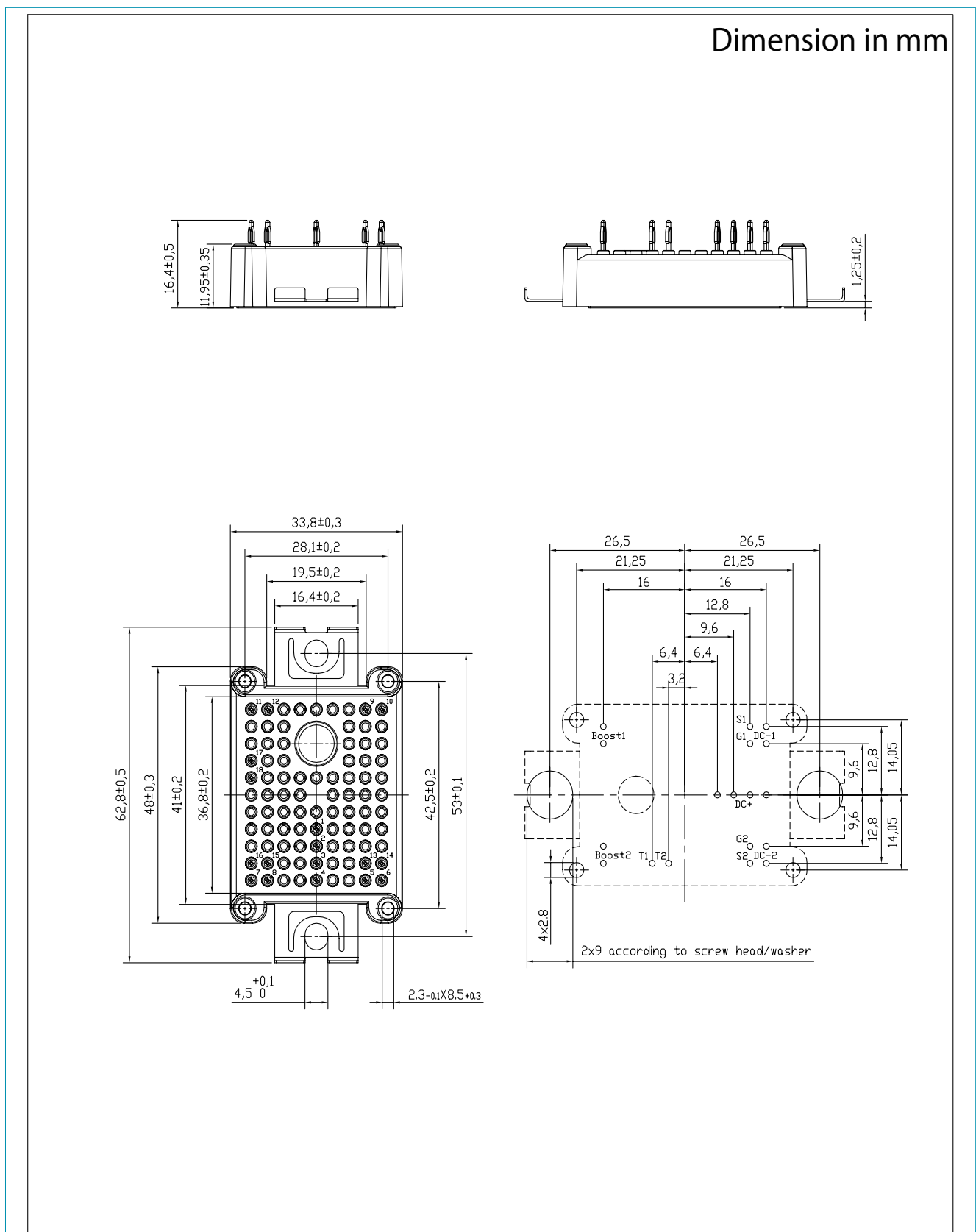


Fig. 25. NTC thermistor resistance as a function of NTC temperature

11. Package outline



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.ween-semi.com>.

### Definitions

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